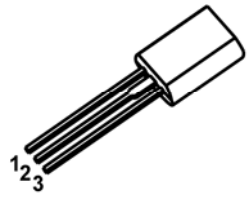
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

3CG751 TRANSISTOR (PNP)

TO-92MOD



FEATURE

- High power amplifier
- Low $V_{CE(sat)}$

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55 to +150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -100μA, I_E=0	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -1 mA , I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA , I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -30 V, I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-2 V, I_C= -500mA	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -1.5 A, I_B= -30mA			-2	V
Transition frequency	f_T	V_{CE}= -5V, I_C= -100mA	50			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			80	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-240	150-400